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Proximity-induced electronic states in epitaxial graphene/SiC (0001) via Tin intercalation

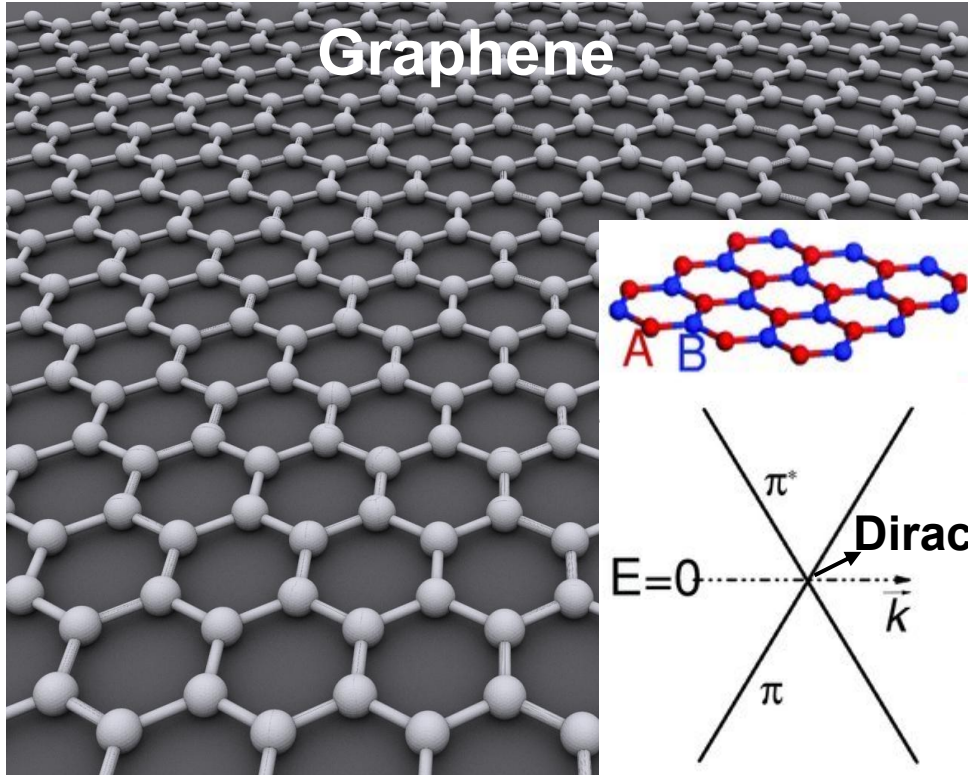
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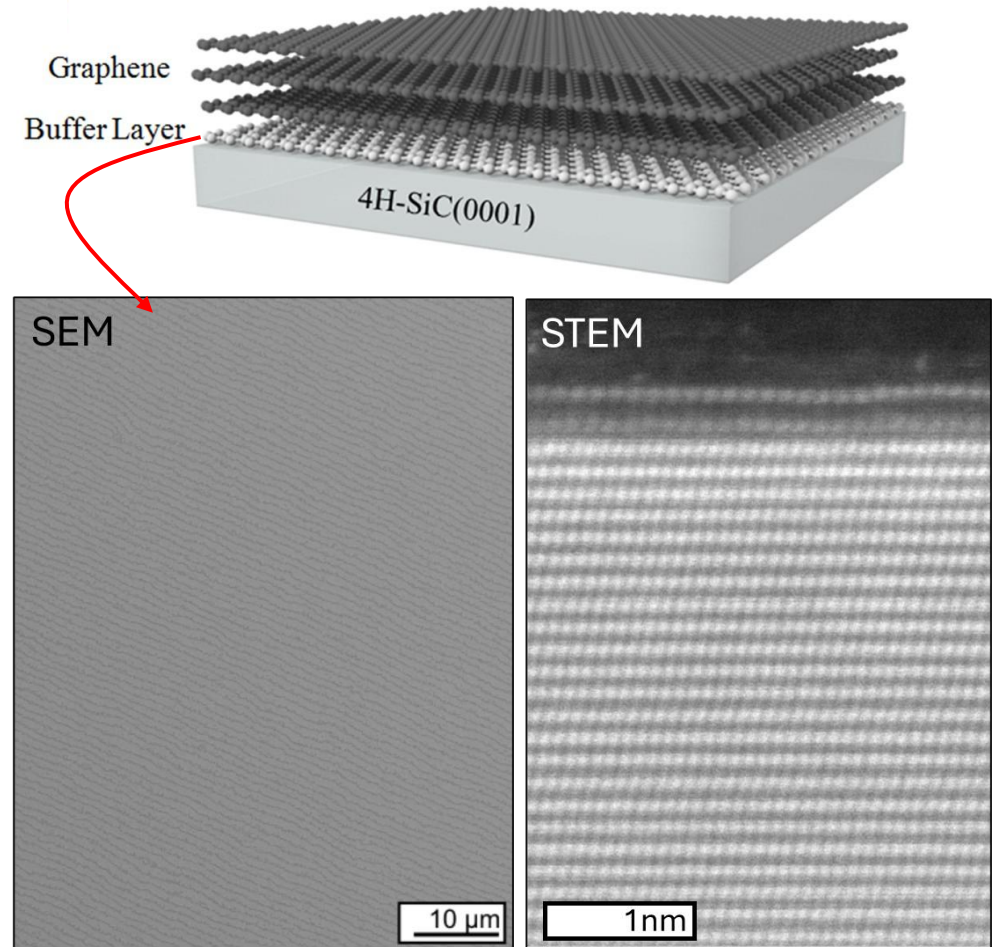
Institute of Physics – Chemnitz University of Technology, Germany



Viet Nam, 9th October 2025

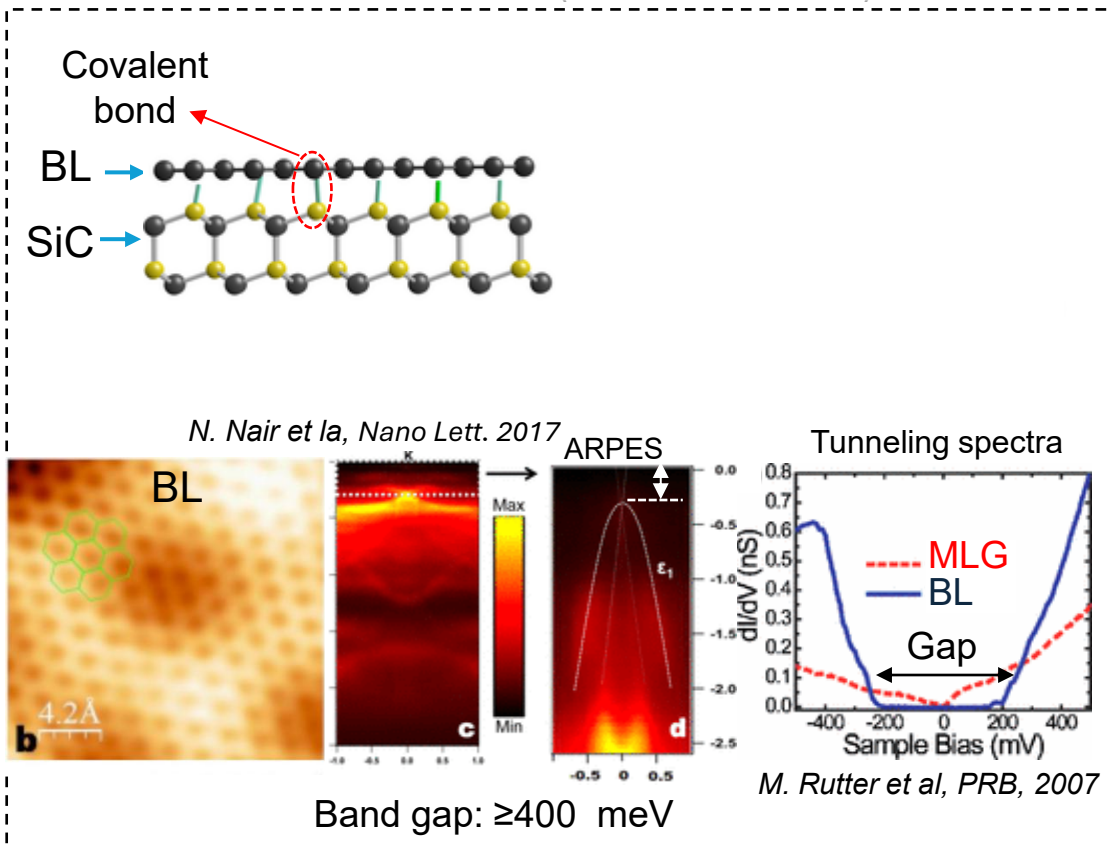


Two symmetric sublattices → Linear band dispersion

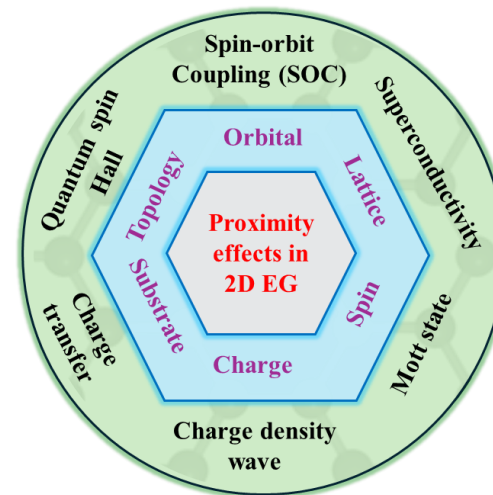
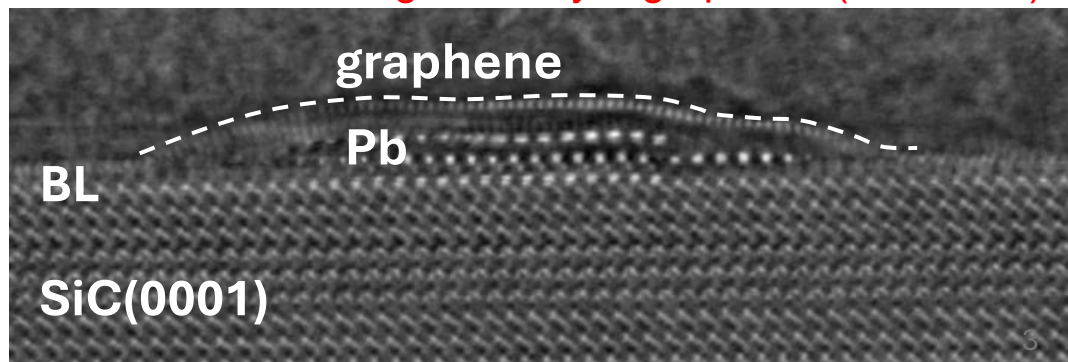


- SiC substrate integration capability
- More scalable and compatible with semiconductor processing.

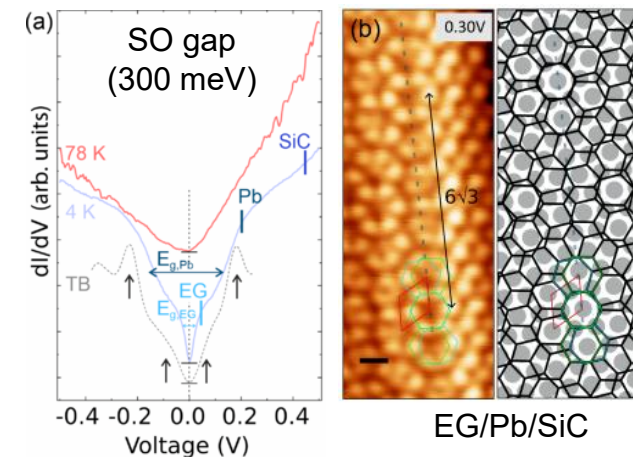
Motivation: Heavy-element intercalation into the buffer layer



Quasi-free-standing monolayer graphene (QFSMLG)

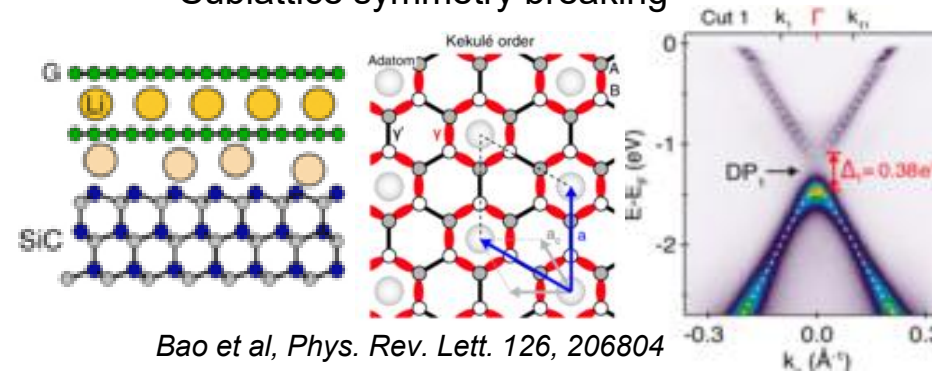


Spin-orbit coupling (SOC) enhancement

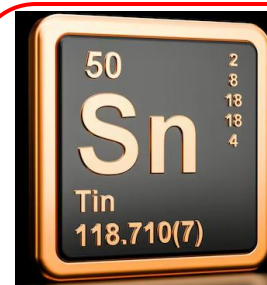


Sublattice symmetry breaking

Ghosal et al, PRL, 2022



Bao et al, Phys. Rev. Lett. 126, 206804



SOC: 72-461 meV

QSH effect (stanene)

Nat Rev Phys 7, 255–269 (2025).

Novel electronic & Structural properties?

Content

01

Sn intercalation-driven metal-insulator transition in epitaxial graphene

Keywords: Scanning tunneling microscopy/spectroscopy (STM/STS), Low Energy Electron Diffraction, Kekulé-graphene, sublattice symmetry breaking, gap opening, charge-neutral graphene, buffer layer (BL), quasi-free-standing monolayer graphene (QFSMGL)

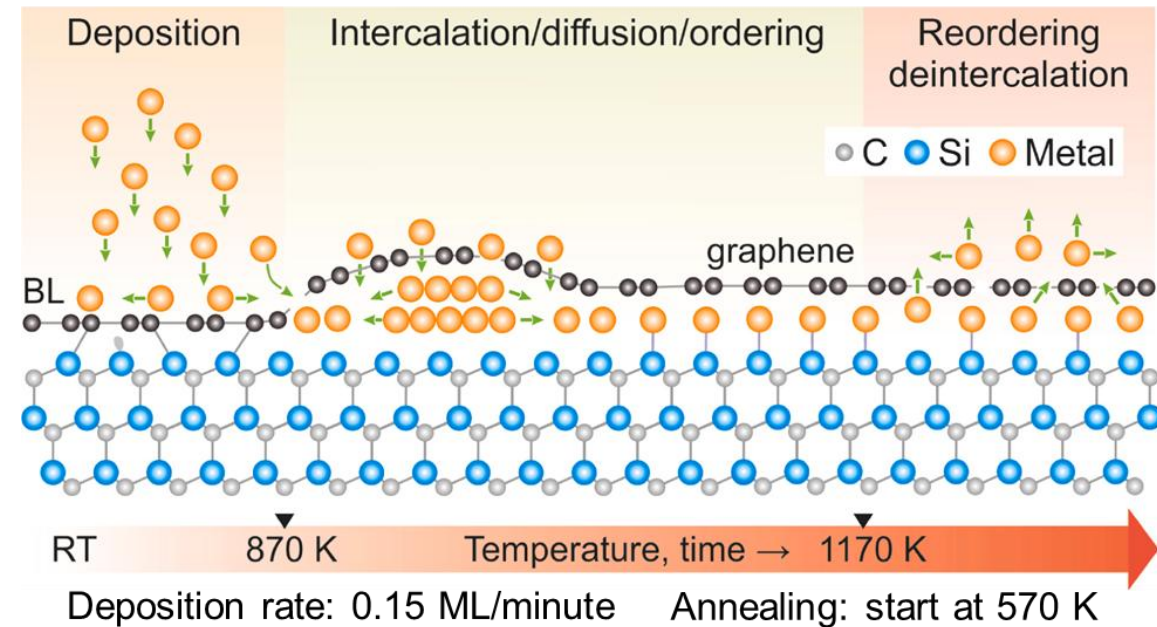
02

Mott states proximitized to a relativistic electron gas in epitaxial graphene

Keywords: $(\sqrt{3} \times \sqrt{3})\text{Sn}$, proximity effects, Mott insulating states, STM/STS, electron energy loss spectroscopy (EELS), pair correlation function (PCF), Dynamical mean-field theory (DMFT) calculations,

1. Sn intercalation-driven metal-insulator transition in epitaxial graphene

Sn(1x1) intercalation into the buffer layer/SiC interface

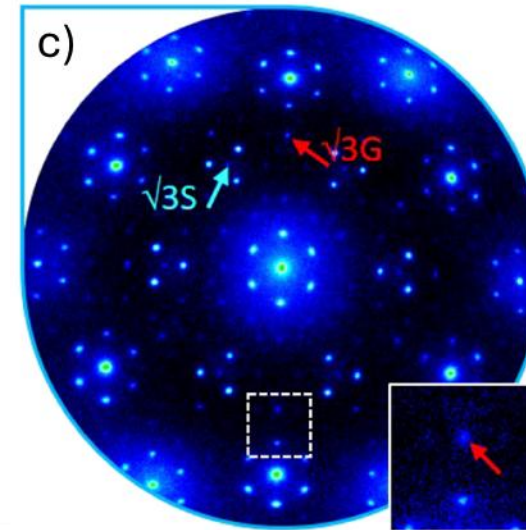


“S”: first-order diffraction spots of SiC(1x1)
 “G”: first-order diffraction spots of EG (1x1)
 “ $\sqrt{3}G$ ”: superlattice of graphene ($a = 4.25 \text{ \AA}$)

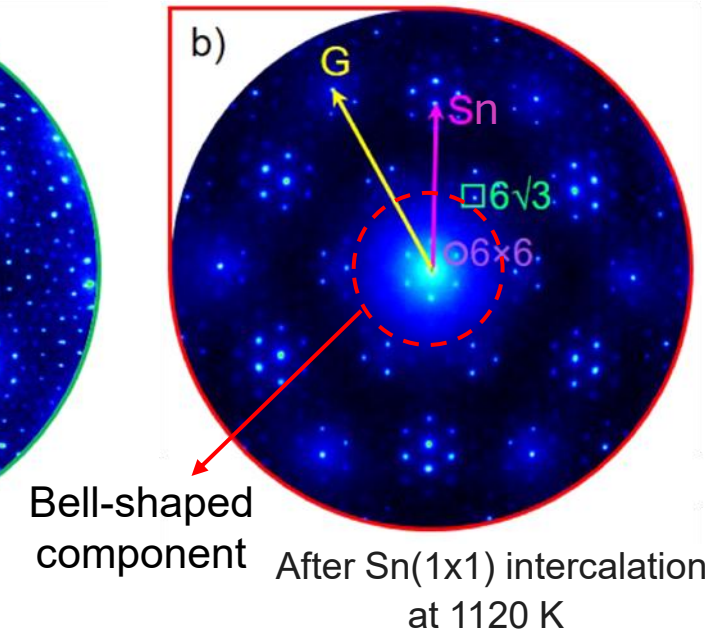
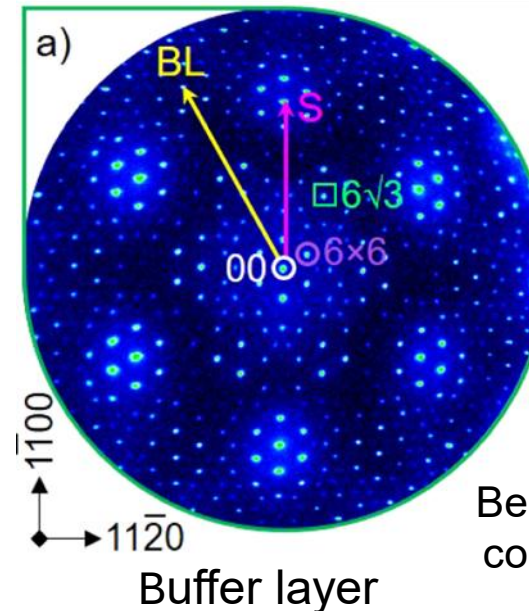
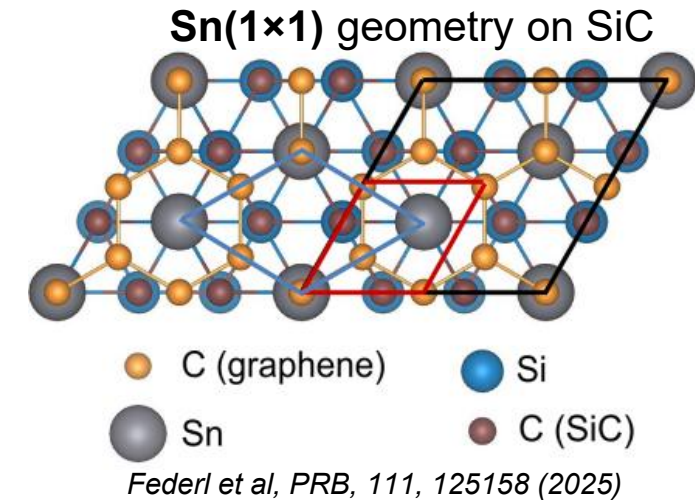
At 1120 K: Quasi-free-standing MLG

At 1320 K: ($\sqrt{3} \times \sqrt{3}G$)R30 wrt Graphene

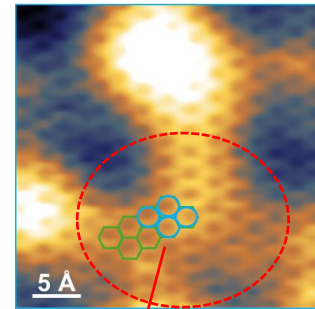
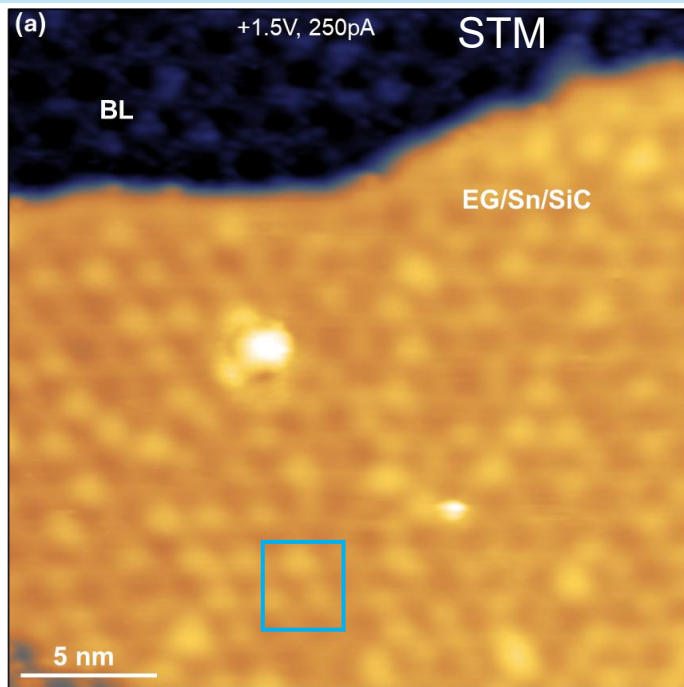
Spot Profile Analysis Low Energy Electron Diffraction (SPA-LEED)



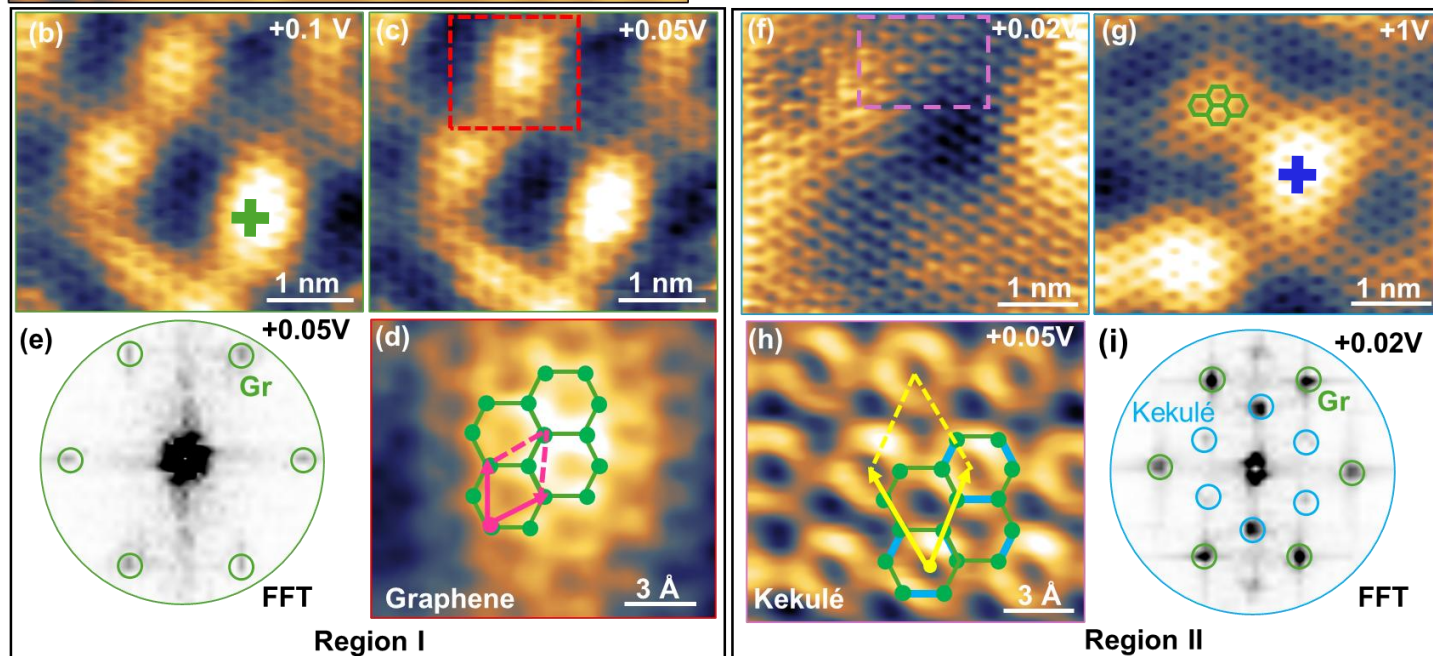
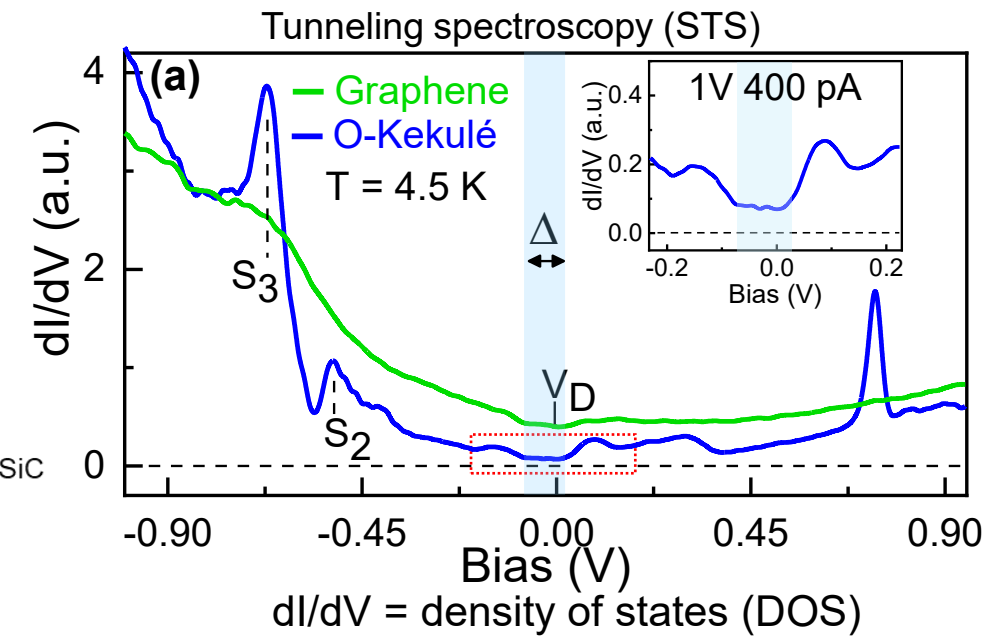
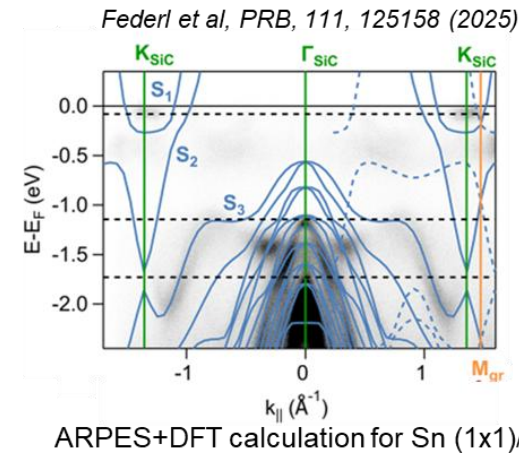
Annealing at 1320 K



Scanning tunneling microscopy/spectroscopy (STM/STS) at 4.5 K



Kekulé-distorted
graphene



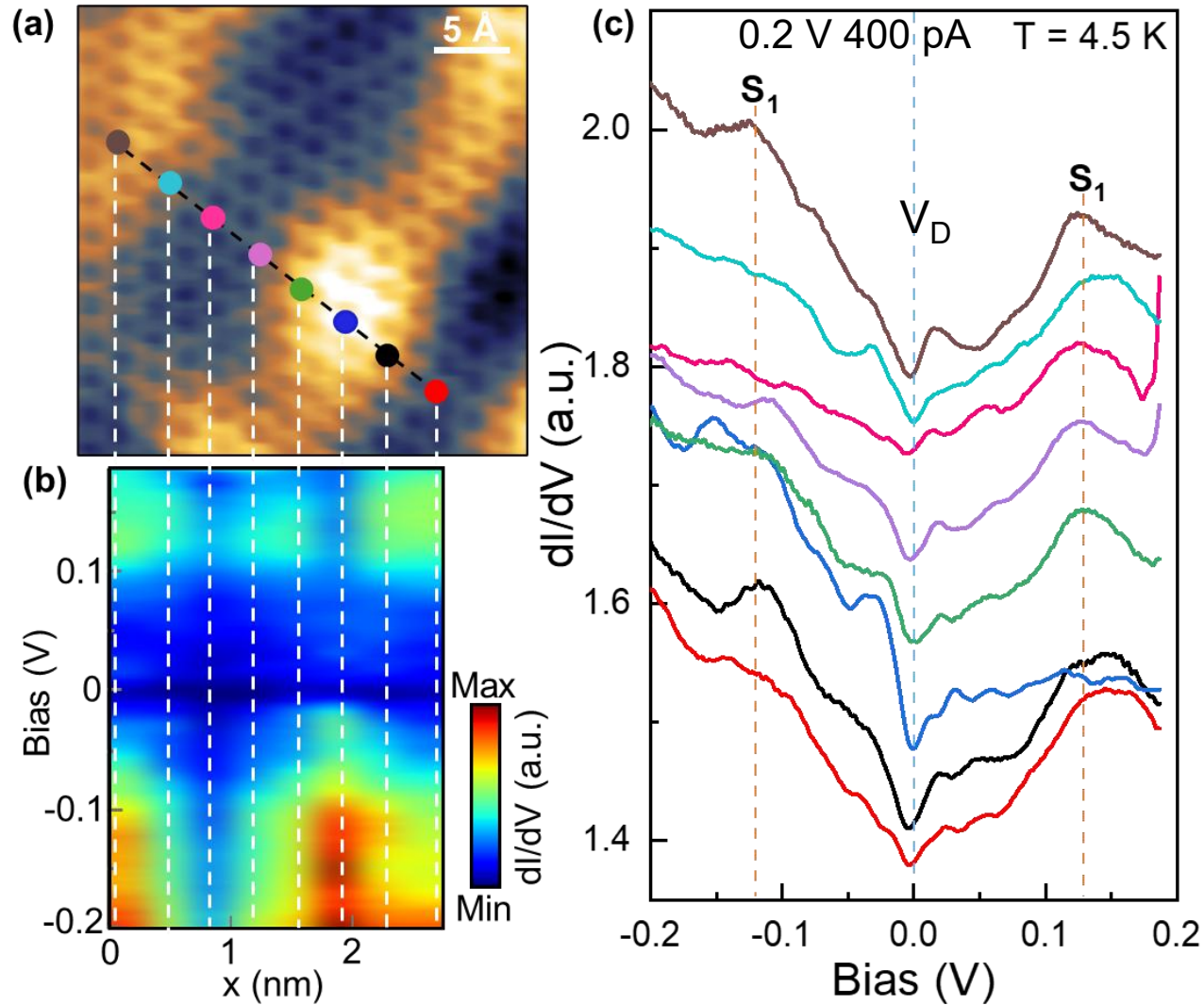
- Linear band dispersion (R1)
- $\text{DOS} > 0 \rightarrow$ Metallic Sn (1x1) phase (RI)
- Gap opening at the DP (Kekulé-O)

Hidden Sn states hint at hybridization with graphene

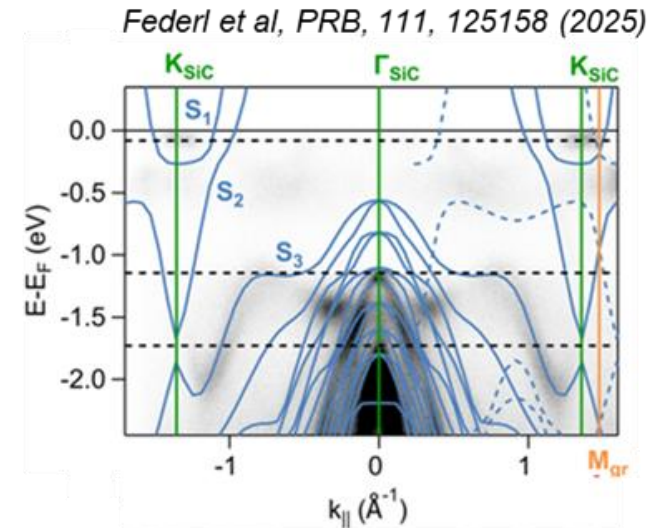
- Kekulé-lattice = $4.25 \text{ \AA} = \sqrt{3} \times a_{Gr}$
- RII: Kekulé-O graphene (+0.02 V)
- RI: graphene + bubble-like features

Sn intercalant-induced charge-neutral graphene probed by STS

Region I: Sn-intercalated buffer layer (no Kekulé)



dI/dV = density of states (DOS)
 V_D : Dirac point voltage



ARPES+DFT calculation for Sn (1x1)/SiC

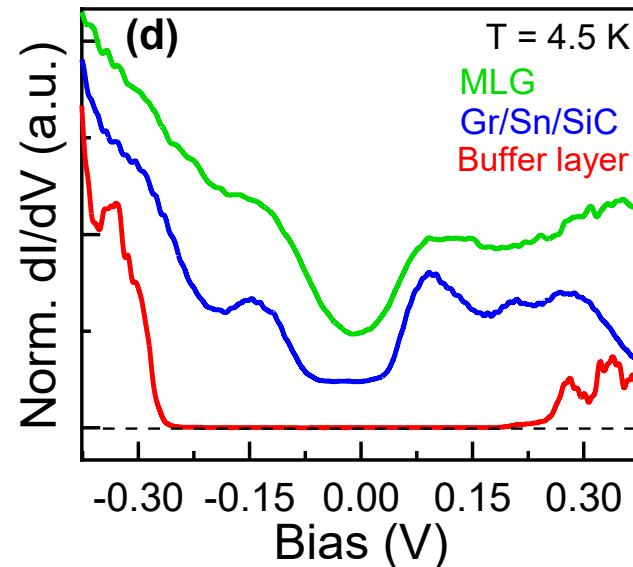
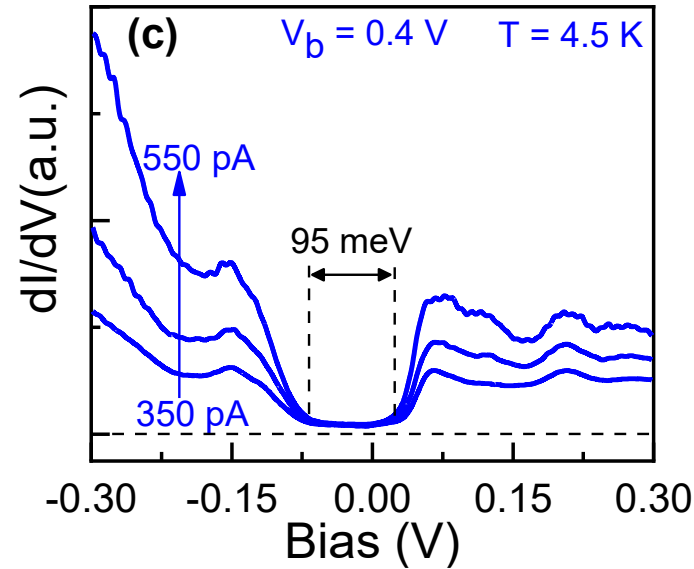
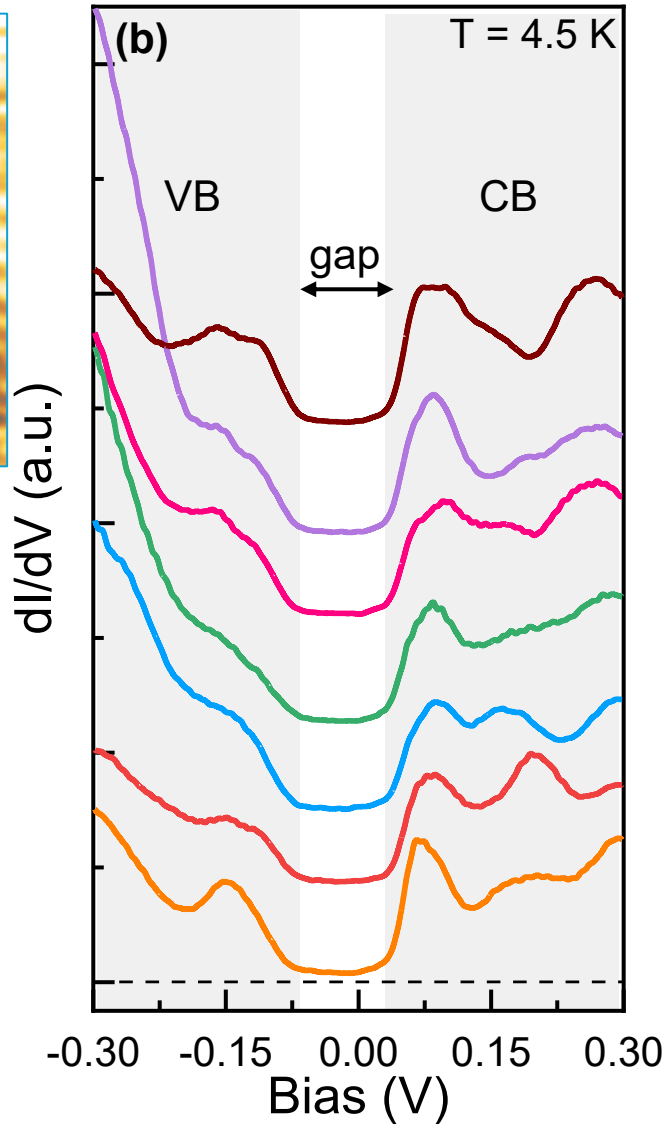
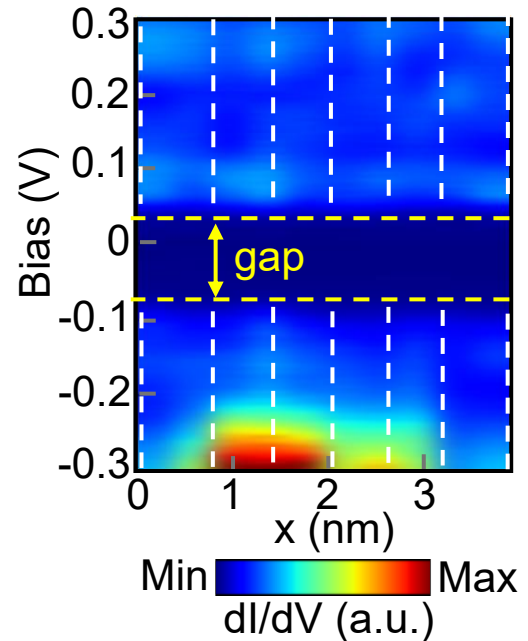
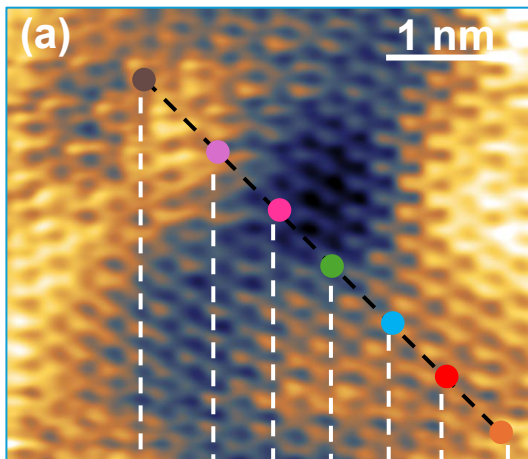
- Charge-neutral graphene (V_D at 0V)
- $DOS > 0 \rightarrow$ Metallic Sn(1x1) phase
- Peaks at ± 0.12 V (S_1 band of Sn layer)



Charge-neutral graphene

Electronic band structure of Kekulé-O graphene probed by STS

Region II: Sn-intercalated buffer layer with Kekulé-O graphene

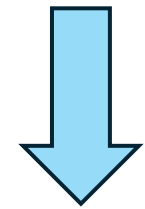


➤ An apparent gap of 95 meV

➤ Stable electronic states

➤ MLG: phonon gap (40 meV)

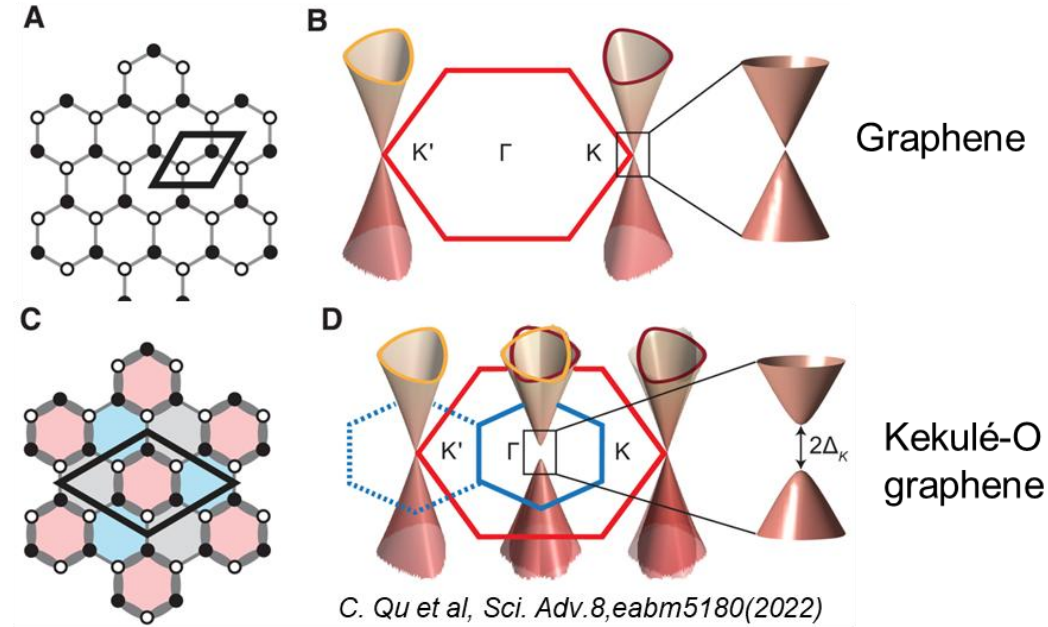
➤ BL gap of 600 meV



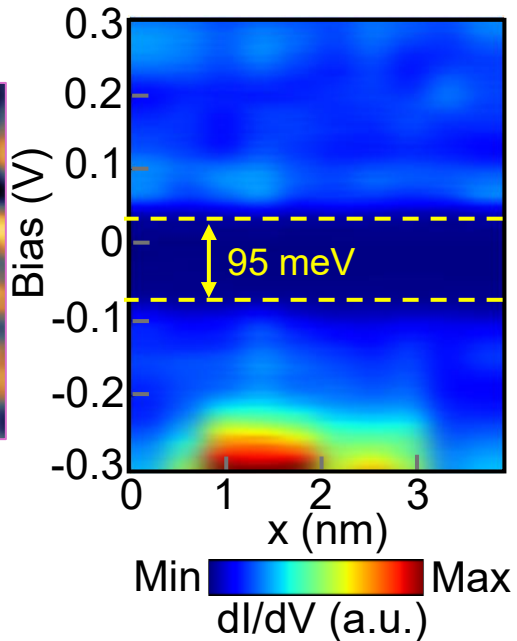
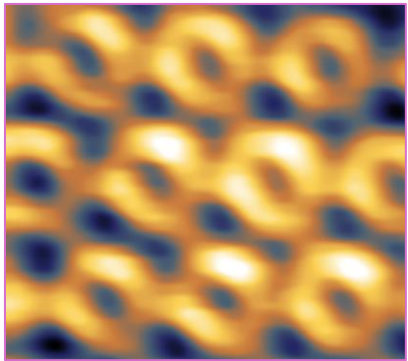
**Sn intercalant-induced
sublattice symmetry breaking**

dI/dV = density of states (DOS)

Energy gap opening in Kekulé-O graphene (Theory)



Kekulé-O graphene



- The energy bands of the Hamiltonian (graphene, K point)

$$E(\mathbf{k}) = \pm \hbar v_F |\vec{k}|$$

sublattice symmetry breaking

- Fold K, K' into the Γ point in the Brillouin zone (kekulé-O)

$$E(\mathbf{k}) = \pm \sqrt{(\hbar v_F |\vec{k}|)^2 + (\Delta^2)} \rightarrow \text{mass term}$$

$$\Rightarrow E_{gap} = 2|\Delta|$$

$$\text{Effective mass of electrons: } m = e^{i\frac{2\pi}{3}} \Delta / (v_F)^2$$

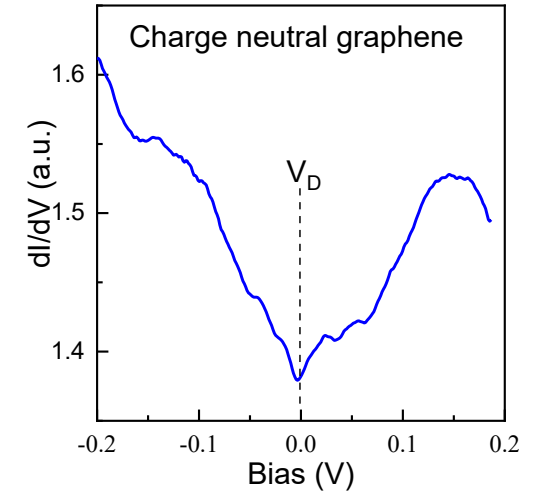
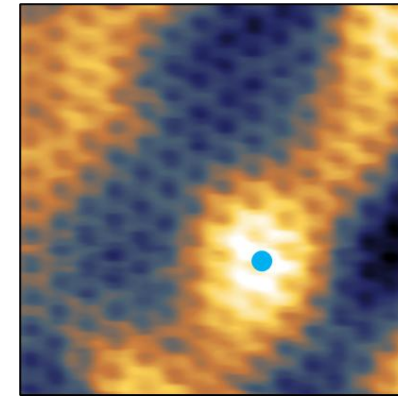
Galván y García et al, Nano Lett. 2024, 24, 7, 2322–2327

Proximity-induced electronic states in epitaxial graphene/SiC (0001) via Tin intercalation

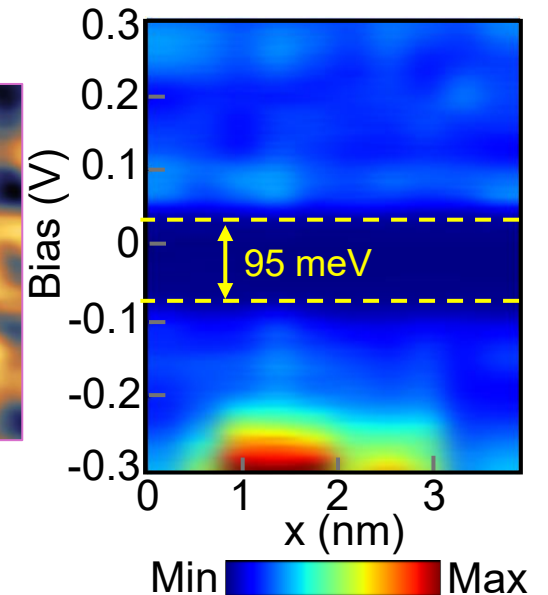
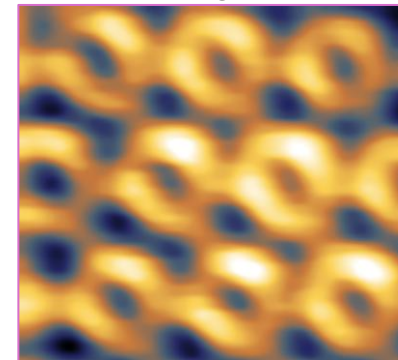
(a) +1V 1 nm

□ Intercalation of Sn into the buffer layer/SiC interface

- Buffer layer is transformed into charge-neutral graphene via the effective charge transfer from Sn intercalants
- Sn(1x1) phase causes the instability of graphene, forming Kekulé-O graphene
- An energy gap (95 meV) opening in Kekulé-O graphene



Kekulé-O graphene



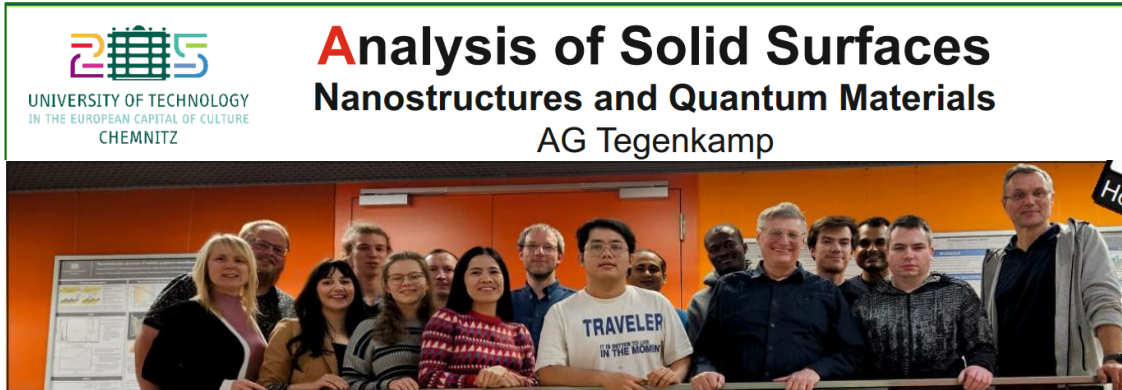
Acknowledgement



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Institute of Physics
TU Chemnitz, Germany



Dr. Zamin Mamiyev



Who we are: The Tegenkamp group focuses on cutting-edge topics in condensed matter physics, including:

- Graphene nanostructures and 2D materials
- Correlation effects in atomic wires and 1D transport
- Electronic and structural properties at solid-state interfaces
- Design of new quantum materials

Our research equipment includes

- Low-temperature (4.5 K, 77 K), various temperatures, and ambient scanning tunneling microscopy/spectroscopy
- SPA-LEED, EELS, Molecular-beam epitaxy (MBE) in UHV
- 4-probes STM + SEM (down to 4.5 K)
- Temperature & Magnetic field-dependent transport (4.5 K, 7 Tesla)
- HR-TEM+EDS, NanoSEM

For Master/PhD's thesis and Postdoc

Contact: Prof. Christoph Tegenkamp

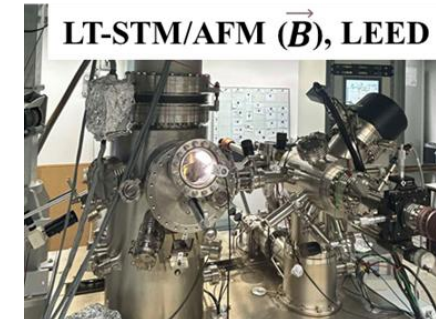
Email: christoph.tegenkamp@physik.tu-chemnitz.de



SCAN ME



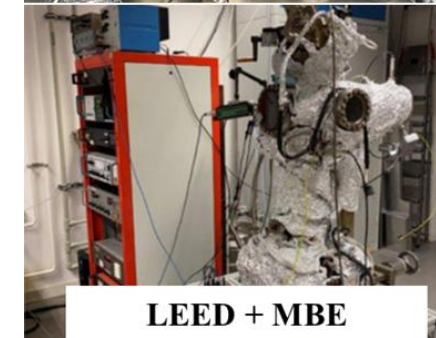
DFG Research Unit:
www.epigraphene.de
(Start: 01/2022)



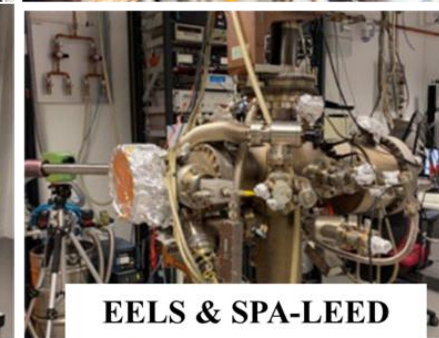
LT-STM/AFM ($\vec{B}$), LEED



4pp-STM/SEM



LEED + MBE



EELS & SPA-LEED



Magnetotransport



NanoSEM

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Thank You !!!